

## **REMARKS**

Claims 1-9 and 11-23 are pending in the application. Claims 1-3, 11-14, 22 and 23 are rejected, and claims 4-9, 11 and 15-21 are objected to. By the present amendment, claims 1, 4, and 11 have been amended. The Examiner's reconsideration on the claim rejections in view of the above amendments and following remarks is respectfully requested.

### **Allowable Subject Matter:**

Applicants gratefully acknowledge the Examiner's indication that claims 4-9 and 15-21 would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

### **Claim Objections:**

Claims 4 and 11 are objected to for the informalities stated on page 2 of the Office Action.

Claims 4 and 11 have been amended as essentially recommended by the Examiner to overcome Examiner's objections. Accordingly, withdrawal of the claim objections is respectfully requested.

### **Claim Rejections- 35 U.S.C. § 102:**

Claims 1, 2, 3, 11-13, 22, and 23 are rejected under 35 U.S.C. 102(e) as being anticipated by Liu et al. (U.S. 6,352,896).

With respect to amended claim 1, amended claim 1 recites, *inter alia*, *the plurality of first SACs and the plurality of second SACs have substantially the same top surface area*. The amendment to claim 1 is supported in the specification, for instance, in Figure 6.

The Examiner contends that Liu teaches each of the plurality of first SACs 222a and each of the plurality of second SACs 222b are substantially the same because they have the same width (Fig. 2D), and it can be broadly and reasonably interpreted as “Substantially same size.”

Liu teaches using a T-shaped island photoresist pattern 218 to form the self-aligned contacts (Col. 6, lines 13-15). Although Liu may disclose a plurality of the first SACs and a plurality of the second SACs having the same width, Liu does not disclose the plurality of first SACs and the plurality second SACs having substantially the same top surface area (See 222a and 222b in Fig. 2D). Thus, Liu does not teach or disclose a plurality of first SACs and a plurality of second SACs having substantially the same top surface area, as essentially claimed in claim 1.

Claims 2, 3, and 9 depend from claim 1. Thus, claims 2, 3, and 9 are believed to be allowable for at least the same reasons as given above for claim 1.

With respect to claim 11, claim 11 recites, *inter alia*, *forming photoresist patterns in a line shape at each of a plurality of rows where there is an absence of any formation of the plurality of active regions*.

The Examiner contends that Liu discloses forming photoresist patterns in a line shape at each of a plurality of rows where there is an absence of any formation of the plurality of active regions because the first row of the photoresist pattern, as shown in Figure 2C of Liu, is a line shape. Applicants respectfully disagree.

Liu teaches that the photoresist pattern 218 is a non-continuous T-shaped island and not a line shaped photoresist pattern (See Col. 4, lines 7-9; Col. 6, lines 13-17). In addition, Figure 2C shows a top a view of a step in the formation of a DRAM capacitor that shows a portion of a photoresist layout. In other words, the photoresist pattern 218 in the top portion of Figure 2C is

cut-off as clearly shown by the cut-off lines at the end of the words lines 216. Further, all of the other photoresist patterns labeled '218' are T-shaped islands, which comports with the description of the 'photoresist patterns 218' given in the specification of Liu. Thus, since Liu specifically teaches forming a non-continuous T-shaped island photoresist pattern 218 throughout its disclosure, Applicants respectfully submit that Liu does not teach or disclose a method for manufacturing a semiconductor device comprising, *inter alia, forming photoresist patterns in a line shape at each of a plurality of rows where there is an absence of any formation of the plurality of active regions*, as claimed in claim 11. Therefore, claim 11 is believed to be patentably distinct over Liu for at least the reasons given above.

Claims 12, 13, 14, 22, and 23 depend from claim 11. Thus, claims 12, 13, 14, 22, and 23 are believed to be allowable for at least the same reasons as given above for claim 11.

Therefore, withdrawal of the claim rejections is respectfully requested.

**Claim Rejections- 35 U.S.C. § 103(a):**

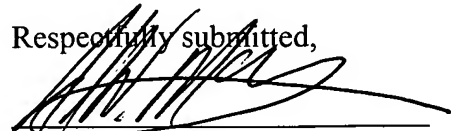
Claim 14 is rejected under 35 U.S.C. §103(a) as being unpatentable over Liu in view of Hurley (U.S. Patent 2003/0013253).

Hurley discloses a fabrication method for forming storage cells in semiconductor devices. Hurley does not disclose a method for manufacturing a semiconductor device comprising, *inter alia, forming photoresist patterns in a line shape at each of a plurality of rows where there is an absence of any formation of the plurality of active regions*, as essentially claimed in claim 11. Thus, Hurley does not cure the deficiencies of Liu.

Since claim 14 is dependent upon claim 11, claim 14 is believed to be allowable for at least the same reasons as stated above for claim 11.

In view of the foregoing remarks and amendments, it is respectfully submitted that all the claims now pending in the application are in condition for allowance. Early and favorable reconsideration of the case is respectfully requested.

Respectfully submitted,



By: Thomas W. McNally  
Reg. No. 48,609  
Attorney for Applicants

F.CHAU & ASSOCIATES, LLC  
1900 Hempstead Turnpike, Suite 501  
East Meadow, NY 11554  
Telephone: (516) 357-0091  
Facsimile: (516) 357-0092